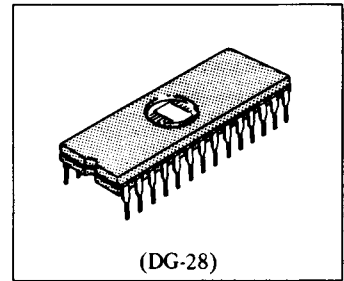


# HN27256G Series

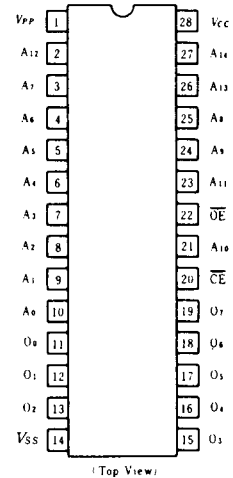
32768-word x 8-bit UV Erasable and Programmable ROM

## ■ FEATURES

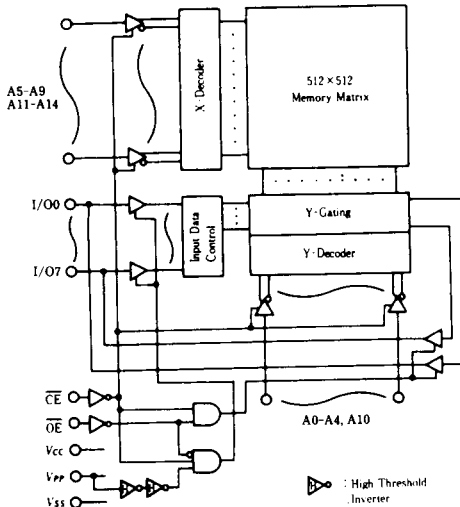
- Single Power Supply . . . . . +5V ± 5%
- High Performance Programming . . . Program Voltage: +12.5V D.C.
- Static . . . . . No Clocks Required
- Inputs and Outputs TTL Compatible During Both Read and Program Modes
- Access Time . . . . . HN27256G-25: 250ns(max.)  
HN27256G-30: 300ns(max.)
- Absolute Max. Rating of  $V_{PP}$  pin . . . 14.0V
- Low Stand-by Current . . . . . 40mA max. (stand-by)
- Device Identifier Mode . . . . . Manufacturer Code and Device Code



## ■ PIN ARRANGEMENT



## ■ BLOCK DIAGRAM



## ■ MODE SELECTION

Mode	Pins	$\overline{CE}$ (20)	$\overline{OE}$ (22)	A9 (24)	$V_{PP}$ (1)	$V_{CC}$ (28)	Outputs (11 - 13, 15 - 19)
Read		$V_{IL}$	$V_{IL}$	X	$V_{CC}$	$V_{CC}$	Dout
Output Disable		$V_{IL}$	$V_{IH}$	X	$V_{CC}$	$V_{CC}$	High Z
Standby		$V_{IH}$	X	X	$V_{CC}$	$V_{CC}$	High Z
High Performance Program		$V_{IL}$	$V_{IH}$	X	$V_{PP}$	$V_{CC}$	Din
Program Verify		$V_{IH}$	$V_{IL}$	X	$V_{PP}$	$V_{CC}$	Dout
Optional Verify		$V_{IL}$	$V_{IL}$	X	$V_{PP}$	$V_{CC}$	Dout
Program Inhibit		$V_{IH}$	$V_{IH}$	X	$V_{PP}$	$V_{CC}$	High Z
Identifier		$V_{IL}$	$V_{IL}$	$V_H^{*2}$	$V_{CC}$	$V_{CC}$	Code

Notes) \*1. X: Don't care.  
\*2.  $V_H$ : 12.0V ± 0.5V.



■ ABSOLUTE MAXIMUM RATING

Item	Symbol	Value	Unit
Operating Temperature Range	$T_{opr}$	0 to +70	°C
Storage Temperature Range	$T_{stg}$	- 65 to +125	°C
Storage Temperature Range Under Bias	$T_{bias}$	- 10 to +80	°C
All Input and Output Voltages*1	$V_{IN}, V_{out}$	-0.6 to +7	V
A9 Input Voltage*1	$V_{ID}$	-0.6 to +13.5	V
$V_{PP}$ Voltage*1	$V_{PP}$	-0.6 to +14.0	V
$V_{CC}$ Voltage*1	$V_{CC}$	-0.6 to +7	V

Note) \*1. with respect to  $V_{SS}$ .

■ READ OPERATION

● DC AND OPERATING CHARACTERISTICS ( $T_a = 0$  to +70°C,  $V_{CC} = 5V \pm 5\%$ ,  $V_{PP} = V_{CC}$ )

Parameter	Symbol	Test Conditions	min.	typ.	max.	Unit
Input Leakage Current	$I_{LI}$	$V_{IN} = 5.25V$	-	-	10	μA
Output Leakage Current	$I_{LO}$	$V_{out} = 5.25V/0.45V$	-	-	10	μA
$V_{PP}$ Current	$I_{PP1}$	$V_{PP} = 5.5 V$	-	-	5	mA
$V_{CC}$ Current (Standby)	$I_{CC1}$	$\overline{CE} = V_{IH}$	-	-	40	mA
$V_{CC}$ Current (Active)	$I_{CC2}$	$\overline{CE} = \overline{OE} = V_{IL}$	-	45	100	mA
Input Low Voltage	$V_{IL}$		-0.1*1	-	0.8	V
Input High Voltage	$V_{IH}$		2.0	-	$V_{CC} + 1$ *2	V
Output Low Voltage	$V_{OL}$	$I_{OL} = 2.1 mA$	-	-	0.45	V
Output High Voltage	$V_{OH}$	$I_{OH} = -400 \mu A$	2.4	-	-	V

\*:  $V_{IL}$  min. = -0.6V for pulse width  $\leq 20ns$ .

\*\* :  $V_{IH}$  max. =  $V_{CC} + 1.5V$  for pulse width  $\leq 20ns$ . If  $V_{IH}$  is over the specified maximum value, read operation cannot be guaranteed.

● AC CHARACTERISTICS ( $T_a=0\sim 70^\circ C$ ,  $V_{CC}=5V \pm 5\%$ ,  $V_{PP} = V_{CC}$ )

Parameter	Symbol	Test Condition	HN27256G-25		HN27256G-30		Unit
			min.	max.	min.	max.	
Address to Output Delay	$t_{ACC}$	$\overline{CE} = \overline{OE} = V_{IL}$	-	250	-	300	ns
$\overline{CE}$ to Output Delay	$t_{CE}$	$\overline{OE} = V_{IL}$	-	250	-	300	ns
$\overline{OE}$ to Output Delay	$t_{OE}$	$\overline{CE} = V_{IL}$	-	100	-	120	ns
$\overline{OE}$ High to Output Float	$t_{DF}$	$\overline{CE} = V_{IL}$	0	60	0	105	ns
Address to Output Hold	$t_{OH}$	$\overline{CE} = \overline{OE} = V_{IL}$	0	-	0	-	ns

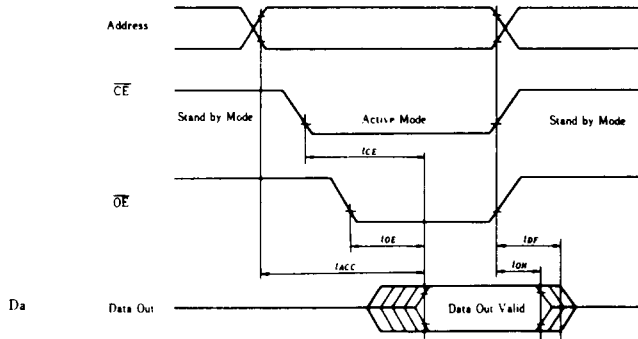
Note:  $t_{DF}$  defines the time at which the Output achieves the open circuit condition and Data is no longer driven.

● SWITCHING CHARACTERISTICS

TEST CONDITION

- Input pulse levels: 0.45V to 2.4V
- Input rise and fall time:  $\leq 20ns$
- Output load: 1 TTL Gate +100pF
- Reference level for measuring timing: 0.8V and 2V



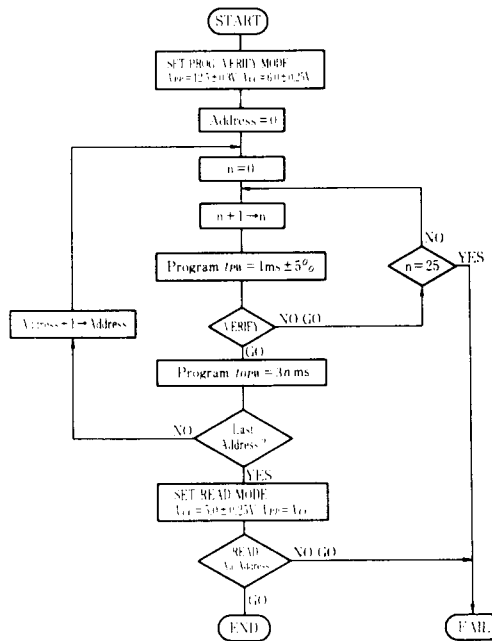


■ CAPACITANCE ( $T_a=25^\circ\text{C}$ ,  $f=1\text{MHz}$ )

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit.
Input Capacitance	$C_{in}$	$V_{in} = 0\text{V}$	—	4	6	pF
Output Capacitance	$C_{out}$	$V_{out} = 0\text{V}$	—	8	12	pF

■ HIGH PERFORMANCE PROGRAMMING

This device can be applied the High Performance Programming algorithm shown in following flowchart. This algorithm allows to obtain faster programming time without any voltage stress to the device nor deterioration in reliability of programmed data.



High Performance Programming Flowchart



■ HIGH PERFORMANCE PROGRAMMING OPERATION

● DC PROGRAMMING CHARACTERISTICS ( $T_a=25^{\circ}\text{C}\pm 5^{\circ}\text{C}$ ,  $V_{CC}=6\text{V}\pm 0.25\text{V}$ ,  $V_{PP}=12.5\text{V}\pm 0.3\text{V}$ )

Parameter	Symbol	Test Condition	min.	typ.	max.	Unit
Input Leakage Current	$I_{LI}$	$V_{IN} = 5.25\text{ V}$	-	-	10	$\mu\text{A}$
Output Low Voltage During Verify	$V_{OL}$	$I_{OL} = 2.1\text{ mA}$	-	-	0.45	V
Output High Voltage During Verify	$V_{OH}$	$I_{OH} = -400\ \mu\text{A}$	2.4	-	-	V
$V_{CC}$ Current (Active)	$I_{CC2}$		-	-	100	mA
Input Low Level	$V_{IL}$		-0.1*1	-	0.8	V
Input High Level	$V_{IH}$		2.0	-	$V_{CC}+0.5$ *2	V
$V_{PP}$ Supply Current	$I_{PP2}$	$\overline{\text{CE}} = V_{IL}$	-	-	50	mA

Notes) \*1. -0.6V for pulse width  $\leq 20\text{ns}$ .

\*2. If  $V_{IH}$  is over the specified maximum value, programming operation cannot be guaranteed.

● AC PROGRAMMING CHARACTERISTICS ( $T_a=25^{\circ}\text{C}\pm 5^{\circ}\text{C}$ ,  $V_{CC}=6\text{V}\pm 0.25\text{V}$ ,  $V_{PP}=12.5\text{V}\pm 0.3\text{V}$ )

Parameter	Symbol	Test Condition	min.	typ.	max.	Unit
Address Setup Time	$t'_{AS}$		2	-	-	$\mu\text{s}$
$\overline{\text{OE}}$ Setup Time	$t'_{OES}$		2	-	-	$\mu\text{s}$
Data Setup Time	$t'_{DS}$		2	-	-	$\mu\text{s}$
Address Hold Time	$t'_{AH}$		0	-	-	$\mu\text{s}$
Data Hold Time	$t'_{DH}$		2	-	-	$\mu\text{s}$
$\overline{\text{OE}}$ to Output Float Delay	$t'_{DF}$ *1		0	-	130	ns
$V_{PP}$ Setup Time	$t'_{VPS}$		2	-	-	$\mu\text{s}$
$V_{CC}$ Setup Time	$t'_{VCS}$		2	-	-	$\mu\text{s}$
$\overline{\text{OE}}$ Pulse Width During Initial Programming	$t_{PW}$		0.95	1.0	1.05	ms
$\overline{\text{CE}}$ Pulse Width During Overprogramming	$t_{OPW}$ *1		2.85	-	78.75	ms
Data Valid from $\overline{\text{OE}}$	$t_{OE}$		-	-	150	ns

Note) \*1.  $t_{OPW}$  is defined as mentioned in flow chart.  $t_{DF}$  defines the time at which the output achieves the open circuit condition and data is no longer driven.

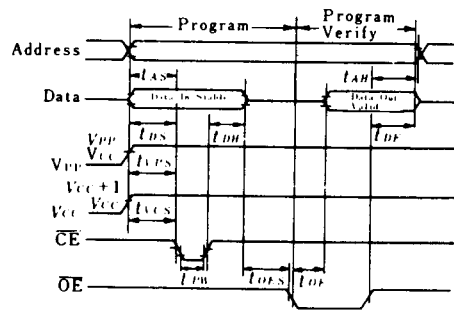
● SWITCHING CHARACTERISTICS

Test Condition

Input pulse level: 0.45 to 2.4V

Input rise and fall time:  $\leq 20\text{ns}$

Reference level for measuring time: 0.8V and 2V



■ ERASE

Erasure of HN27256G is performed by exposure to ultraviolet light of 2537Å and all the output data are changed to "1" after this erasure procedure. The minimum integrated dose (i.e. UV intensity x exposure time) for erasure is 15W. sec/cm<sup>2</sup>.

■ DEVICE IDENTIFIER MODE

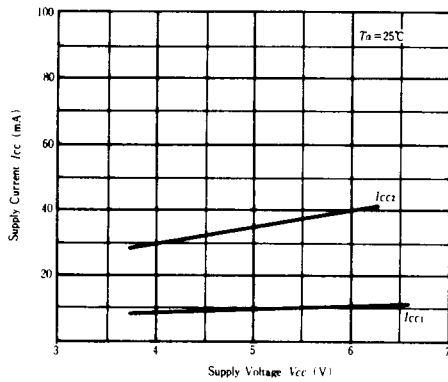
The Identifier Mode allows the reading out of binary codes that identify Manufacturer and type of device, from outputs of EPROM. By this Mode, the device will be automatically matched its own corresponding programming algorithm, using programming equipment.

● HN27256G SERIES IDENTIFIER CODE

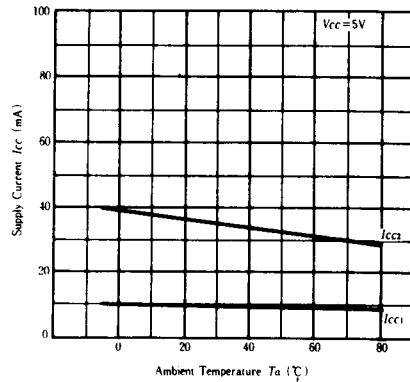
Identifier	Pins	A <sub>0</sub> (10)	O <sub>7</sub> (19)	O <sub>6</sub> (18)	O <sub>5</sub> (17)	O <sub>4</sub> (16)	O <sub>3</sub> (15)	O <sub>2</sub> (13)	O <sub>1</sub> (12)	O <sub>0</sub> (11)	Hex Data
Manufacturer Code	<i>V<sub>IL</sub></i>	0	0	0	0	0	0	1	1	1	07
Device Code	<i>V<sub>IH</sub></i>	0	0	0	0	1	0	0	0	0	10

Notes: 1. A<sub>9</sub> = 12.0V ± 0.5V.  
 2. A<sub>1</sub> - A<sub>8</sub>, A<sub>10</sub> - A<sub>14</sub>,  $\overline{CE}$ ,  $\overline{OE}$  = *V<sub>IL</sub>*.

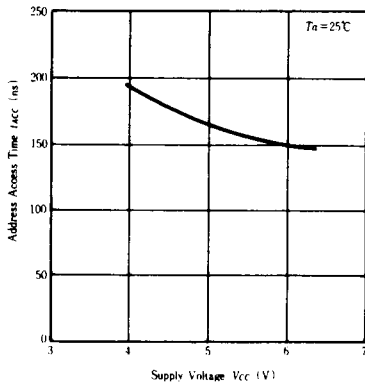
SUPPLY CURRENT VS. SUPPLY VOLTAGE



SUPPLY CURRENT VS. AMBIENT TEMPERATURE



ADDRESS ACCESS TIME VS. SUPPLY VOLTAGE



ADDRESS ACCESS TIME VS. AMBIENT TEMPERATURE

